Albert Romano-Rodriguez

List of Publications by Year
in descending order

169	5,949	71102	76900
papers	citations	41 h-index	74 g-index

170	170	170	6278
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Nitrogen Dioxide Selective Sensor for Humid Environments Based on Octahedral Indium Oxide. Frontiers in Sensors, 2021, 2, .	3.3	2
2	A Novel Approach for a Chip-Sized Scanning Optical Microscope. Micromachines, 2021, 12, 527.	2.9	1
3	Pursuing the Diffraction Limit with Nano-LED Scanning Transmission Optical Microscopy. Sensors, 2021, 21, 3305.	3.8	4
4	Fabrication, Characterization and Performance of Low Power Gas Sensors Based on (GaxIn1-x)2O3ÂNanowires. Sensors, 2021, 21, 3342.	3.8	3
5	Hybrid liquid crystalline zinc phthalocyanine@Cu2O nanowires for NO2 sensor application. Sensors and Actuators B: Chemical, 2021, 345, 130431.	7.8	8
6	Inorganic nanomaterials. , 2020, , 17-35.		0
7	Nano illumination microscopy: a technique based on scanning with an array of individually addressable nanoLEDs. Optics Express, 2020, 28, 19044.	3.4	18
8	Room Temperature Humidity Sensor Based on Single Î²-Ga2O3 Nanowires. Proceedings (mdpi), 2019, 2, .	0.2	5
9	Electron beam lithography for contacting single nanowires on non-flat suspended substrates. Sensors and Actuators B: Chemical, 2019, 286, 616-623.	7.8	7
10	Site-Specific Growth and in Situ Integration of Different Nanowire Material Networks on a Single Chip: Toward a Nanowire-Based Electronic Nose for Gas Detection. ACS Sensors, 2018, 3, 727-734.	7.8	31
11	Selectively arranged single-wire based nanosensor array systems for gas monitoring. Nanoscale, 2018, 10, 9087-9096.	5.6	19
12	Electrical Impedance Spectroscopy Microflow Cytometer for Cell Viability Tests. , 2018, , .		3
13	A Compact Robust OWLS System for Biosensing of Multiple Samples. Proceedings (mdpi), 2018, 2, .	0.2	0
14	Localized and In-Situ Integration of Different Nanowire Materials for Electronic Nose Applications. Proceedings (mdpi), 2018, 2, 957.	0.2	1
15	Comparative Studies of Chemoresistive Gas Sensors Based on Multiple Randomly Connected Wires and Arrays of Single-Wires. Proceedings (mdpi), 2018, 2, .	0.2	0
16	Different Nanowire Materials Localized Growth and In-Situ Integration for Electronic Nose Applications. , 2018, , .		0
17	Electrical Impedance Spectroscopy Microflow Cytometer for Cell Viability Tests. , 2018, , .		0
18	Low temperature humidity sensor based on Ge nanowires selectively grown on suspended microhotplates. Sensors and Actuators B: Chemical, 2017, 243, 669-677.	7.8	23

#	Article	IF	Citations
19	Colorimetric sensor for bad odor detection using automated color correction. , 2017, , .		1
20	Pushing the Composition Limit of Anisotropic Ge_{1â€“x}Sn_x Nanostructures and Determination of Their Thermal Stability. Chemistry of Materials, 2017, 29, 9802-9813.	6.7	33
21	Gas sensors based on individual indium oxide nanowire. Sensors and Actuators B: Chemical, 2017, 238, 447-454.	7.8	44
22	Gas Sensors Based on Individual (Ga, In)2O3 Nanowires. Proceedings (mdpi), 2017, 1, 321.	0.2	1
23	Laser Interferometry for Broad Area SPR-Grating Couplers in Chemical Applications. Proceedings (mdpi), 2017, 1, .	0.2	0
24	Gas Sensing Characterization of Single-Nanowire Sensor Array Systems Based on Non-Functionalized and Pt-Functionalized Tungsten Oxide. Proceedings (mdpi), 2017, 1, .	0.2	1
25	Individual Gallium Oxide Nanowires for Humidity Sensing at Low Temperature. Proceedings (mdpi), 2017, 1, .	0.2	4
26	Functional materials for environmental sensors and energy systems. Beilstein Journal of Nanotechnology, 2017, 8, 2015-2016.	2.8	1
27	Nanosensor array systems based on single functional wires selectively integrated and their sensing properties to C2H6O and NO2. , 2017, , .		1
28	Site-selectively Grown p-type Ge NWs as a Gas Sensor. Procedia Engineering, 2016, 168, 1056-1060.	1.2	0
29	Optical particle detection in liquid suspensions with a hybrid integrated microsystem. Sensors and Actuators A: Physical, 2016, 247, 629-640.	4.1	5
30	Site-selectively grown SnO2 NWs networks on micromembranes for efficient ammonia sensing in humid conditions. Sensors and Actuators B: Chemical, 2016, 232, 402-409.	7.8	31
31	Formaldehyde sensing mechanism of SnO₂ nanowires grown on-chip by sputtering techniques. RSC Advances, 2016, 6, 18558-18566.	3.6	15
32	Optical Particle Detection in Liquid Suspensions with a Hybrid Integrated Microsystem. Procedia Engineering, 2015, 120, 1071-1074.	1.2	0
33	Gas Nanosensors Based on Individual Indium Oxide Nanostructures. Procedia Engineering, 2015, 120, 795-798.	1.2	6
34	Locally Grown SnO 2 NWs as Low Power Ammonia Sensor. Procedia Engineering, 2015, 120, 215-219.	1.2	4
35	Low-cost Fabrication of Zero-power Metal Oxide Nanowire Gas Sensors: Trends and Challenges. Procedia Engineering, 2015, 120, 488-491.	1.2	2
36	Facile integration of ordered nanowires in functional devices. Sensors and Actuators B: Chemical, 2015, 221, 104-112.	7.8	27

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37	Hybrid integration of VCSELs and microlenses for a particle detection microoptical system. , 2015, , .		0
38	Low resistivity Pt interconnects developed by electron beam assisted deposition using novel gas injector system. Journal of Physics: Conference Series, 2012, 371, 012038.	0.4	1
39	SiC-based MIS gas sensor for high water vapor environments. Sensors and Actuators B: Chemical, 2012, 175, 60-66.	7.8	17
40	Localized growth and in situ integration of nanowires for device applications. Chemical Communications, 2012, 48, 4734.	4.1	32
41	SiC-Based MIS Gas Sensor for High Water Vapor Environments. Procedia Engineering, 2011, 25, 1321-1324.	1.2	0
42	Methods and Techniques for the Fabrication of Gas Sensing Devices from Nanowires. Procedia Engineering, 2011, 25, 1409-1412.	1.2	0
43	Harnessing self-heating in nanowires for energy efficient, fully autonomous and ultra-fast gas sensors. Sensors and Actuators B: Chemical, 2010, 144, 1-5.	7.8	42
44	Experimental study of the retention properties of a cyclo olefin polymer pillar array column in reversedâ€phase mode. Journal of Separation Science, 2010, 33, 3313-3318.	2.5	9
45	Synthesis and applications of one-dimensional semiconductors. Progress in Materials Science, 2010, 55, 563-627.	32.8	450
46	Experimental study of the depth influence on the band broadening effect in a cyclo-olefin polymer column containing an array of ordered pillars. Journal of Chromatography A, 2010, 1217, 5817-5821.	3.7	15
47	A cyclo olefin polymer microfluidic chip with integrated gold microelectrodes for aqueous and non-aqueous electrochemistry. Lab on A Chip, 2010, 10, 1254.	6.0	49
48	Room temperature conductometric gas sensors based on metal oxide nanowires and nanocrystals. , 2009, , .		2
49	Direct observation of the gas-surface interaction kinetics in nanowires through pulsed self-heating assisted conductometric measurements. Applied Physics Letters, 2009, 95, .	3.3	33
50	Photoexcited Individual Nanowires: Key Elements in Room Temperature Detection of Oxidizing Gases. , 2009, , .		1
51	Mesoporous Silica: A Suitable Adsorbent for Amines. Nanoscale Research Letters, 2009, 4, 1303-8.	5.7	19
52	Detection of amines with chromium-doped WO3 mesoporous material. Sensors and Actuators B: Chemical, 2009, 140, 557-562.	7.8	51
53	Equivalence between thermal and room temperature UV light-modulated responses of gas sensors based on individual SnO2 nanowires. Sensors and Actuators B: Chemical, 2009, 140, 337-341.	7.8	195
54	Ultimate response dynamics achieved with gas sensors based on self-heated nanowires. Procedia Chemistry, 2009, 1, 1427-1430.	0.7	3

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55	Studies on Surface Facets and Chemical Composition of Vapor Grown One-Dimensional Magnetite Nanostructures. Crystal Growth and Design, 2009, 9, 1077-1081.	3.0	36
56	A model for the response towards oxidizing gases of photoactivated sensors based on individual SnO2 nanowires. Physical Chemistry Chemical Physics, 2009, 11, 10881.	2.8	63
57	On the role of individual metal oxide nanowires in the scaling down of chemical sensors. Physical Chemistry Chemical Physics, 2009, 11, 7105.	2.8	77
58	Individual nanowire chemical sensor system self-powered with energy scavenging technologies. , 2009, , .		2
59	An array of ordered pillars with retentive properties for pressure-driven liquid chromatography fabricated directly from an unmodified cyclo olefin polymer. Lab on A Chip, 2009, 9, 1511.	6.0	31
60	UV photosensors based on individual semiconductor nanowires. , 2009, , .		0
61	An experimental method to estimate the temperature of individual nanowires. International Journal of Nanotechnology, 2009, 6, 860.	0.2	12
62	Nanosensors: Controlling Transduction Mechanisms at the Nanoscale Using Metal Oxides and Semiconductors. , 2009, , 1-51.		1
63	Nano- and microsized metal oxide thin film gas sensors. Microsystem Technologies, 2008, 14, 645-651.	2.0	10
64	Insight into the Role of Oxygen Diffusion in the Sensing Mechanisms of SnO₂ Nanowires. Advanced Functional Materials, 2008, 18, 2990-2994.	14.9	96
65	Chemical Vapor Growth of Oneâ€dimensional Magnetite Nanostructures. Advanced Materials, 2008, 20, 1550-1554.	21.0	92
66	Nanostructured oxides on porous silicon microhotplates for NH3 sensing. Microelectronic Engineering, 2008, 85, 1116-1119.	2.4	14
67	Localized-mass detection based on thin-film bulk acoustic wave resonators (FBAR): Area and mass location aspects. Sensors and Actuators A: Physical, 2008, 142, 322-328.	4.1	22
68	Ultralow power consumption gas sensors based on self-heated individual nanowires. Applied Physics Letters, 2008, 93, .	3.3	184
69	Toward a Systematic Understanding of Photodetectors Based on Individual Metal Oxide Nanowires. Journal of Physical Chemistry C, 2008, 112, 14639-14644.	3.1	130
70	Gas Sensing Devices Based on 1D Metal-Oxide Nanostructures: Fabrication, Testing and Device Integration. ECS Transactions, 2008, 13, 57-64.	0.5	0
71	The effects of electronâ€“hole separation on the photoconductivity of individual metal oxide nanowires. Nanotechnology, 2008, 19, 465501.	2.6	169
72	Fabrication of bottom-up gas sensors based on individual SnO₂ nanowires and suspended microhotplates. , 2007, , .		0

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73	Nano and micro stripe based metal oxide thin film gas sensor. , 2007, , .		0
74	Bottom-up Fabrication of Individual SnO2 Nanowires-based Gas Sensors on Suspended Micromembranes. Materials Research Society Symposia Proceedings, 2007, 1052, 1.	0.1	0
75	Micro and nanotechnologies for the development of an integrated chromatographic system. , 2007, , .		2
76	Template synthesis and forming electrical contacts to single Au nanowires by focused ion beam techniques. Nanotechnology, 2007, 18, 459001.	2.6	1
77	Electrical properties of individual tin oxide nanowires contacted to platinum electrodes. Physical Review B, 2007, 76, .	3.2	105
78	Raman microprobe characterization of electrodeposited S-rich CuIn(S,Se)2 for photovoltaic applications: Microstructural analysis. Journal of Applied Physics, 2007, 101, 103517.	2.5	66
79	Electrodeposited CuIn(S, Se)2 films for low cost high efficiency solar cell applications: microstructural analysis. , 2007, , .		1
80	Water vapor detection with individual tin oxide nanowires. Nanotechnology, 2007, 18, 424016.	2.6	59
81	Focused-ion-beam-assisted tuning of thin-film bulk acoustic wave resonators (FBARs). Journal of Micromechanics and Microengineering, 2007, 17, 2380-2389.	2.6	9
82	Portable microsensors based on individual SnO₂nanowires. Nanotechnology, 2007, 18, 495501.	2.6	68
83	Effect of the nanostructure and surface chemistry on the gas adsorption properties of macroscopic multiwalled carbon nanotube ropes. Carbon, 2007, 45, 83-88.	10.3	16
84	Dual-beam focused ion beam (FIB): A prototyping tool for micro and nanofabrication. Microelectronic Engineering, 2007, 84, 789-792.	2.4	18
85	High response and stability in CO and humidity measures using a single SnO2 nanowire. Sensors and Actuators B: Chemical, 2007, 121, 3-17.	7.8	165
86	P2K-2 Sensitivity Considerations in Localized Mass Detection Based on Thin-Film Bulk Acoustic Wave Resonators. , 2006, , .		2
87	Localized and distributed mass detectors with high sensitivity based on thin-film bulk acoustic resonators. Applied Physics Letters, 2006, 89, 033507.	3.3	45
88	Fabrication and electrical characterization of circuits based on individual tin oxide nanowires. Nanotechnology, 2006, 17, 5577-5583.	2.6	135
89	Electrical Contacts and Gas Sensing Analysis of Individual Metal Oxide Nanowires and 3-D Nanocrystal Networks. IEEJ Transactions on Sensors and Micromachines, 2006, 126, 537-547.	0.1	4
90	Characterization of metal-oxide nanosensors fabricated with focused ion beam (FIB). Sensors and Actuators B: Chemical, 2006, 118, 198-203.	7.8	42

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91	Analyses of the ammonia response of integrated gas sensors working in pulsed mode. Sensors and Actuators B: Chemical, 2006, 118, 318-322.	7.8	28
92	Fabrication of metallic contacts to nanometre-sized materials using a focused ion beam (FIB). Materials Science and Engineering C, 2006, 26, 1063-1066.	7.3	57
93	Template synthesis and forming electrical contacts to single Au nanowires by focused ion beam techniques. Nanotechnology, 2006, 17, 1134-1139.	2.6	40
94	Characterisation and stabilisation of Pt/TaSix/SiO2/SiC gas sensor. Sensors and Actuators B: Chemical, 2005, 109, 119-127.	7.8	10
95	In situ and ex situ characterisation of thermally induced crystallisation of CuInS2 thin films for solar cell. Thin Solid Films, 2005, 480-481, 362-366.	1.8	20
96	Vibrational and crystalline properties of polymorphicCuInC2(C=Se,S)chalcogenides. Physical Review B, 2005, 71, .	3.2	86
97	Estudio de la reacciÃ³n de sulfurizaciÃ³n de precursores Cu/In para la formaciÃ³n de capas delgadas policristalinas de CuInS₂ para cÃ©lulas solares. Boletin De La Sociedad Espanola De Ceramica Y Vidrio, 2004, 43, 348-351.	1.9	0
98	Transmission electron microscopy and image simulation study of CuAu domains in CuInS2 epitaxial layers. Thin Solid Films, 2003, 431-432, 226-230.	1.8	2
99	Growth process monitoring and crystalline quality assessment of CuInS(Se)2 based solar cells by Raman spectroscopy. Thin Solid Films, 2003, 431-432, 122-125.	1.8	50
100	Real-time investigations of the influence of sodium on the properties of Cu-poor prepared CuInS2 thin films. Thin Solid Films, 2003, 431-432, 110-115.	1.8	20
101	Porous-like silicon prepared from Si:H annealed at high argon pressure. Physica Status Solidi A, 2003, 197, 236-240.	1.7	3
102	Short-channel radiation effect in 60 MeV proton irradiated 0.13Î¼m CMOS transistors. IEEE Transactions on Nuclear Science, 2003, 50, 2426-2432.	2.0	61
103	Sulfurization of Cu/In Precursors for CuInS[sub 2]-Based Solar Cells. Journal of the Electrochemical Society, 2003, 150, G400.	2.9	11
104	<title>Raman scattering and microstructural analysis of polycrystalline CuInS2 films for solar cell devices</title>. , 2003, 5024, 117.		1
105	Polymorphism in CuInS2 epilayers: Origin of additional Raman modes. Applied Physics Letters, 2002, 80, 562-564.	3.3	74
106	Luminescence and Morphological Properties of GaN Layers Grown on SiC/Si(111) Substrates. Physica Status Solidi A, 2002, 192, 401-406.	1.7	2
107	Growth of GaN layers on SiC/Si(111) substrate by molecular beam epitaxy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 93, 172-176.	3.5	16
108	The complete Raman spectrum of nanometric SnO2 particles. Journal of Applied Physics, 2001, 90, 1550-1557.	2.5	686

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109	Strain in hydrogen and oxygen implanted silicon and SOI structures annealed at high pressure. Journal of Alloys and Compounds, 2001, 328, 181-186.	5.5	6
110	Microstructure of Czochralski silicon annealed at enhanced stress conditions. Journal of Alloys and Compounds, 2001, 328, 90-96.	5.5	8
111	Effect of uniform stress on silicon implanted with helium, hydrogen and oxygen. Computational Materials Science, 2001, 21, 515-525.	3.0	16
112	<title>Effect of stress on defect transformation in hydrogen-implanted silicon and SOI structures</title>. , 2001, 4412, 120.		1
113	Effect of annealing at argon pressure up to 1.2 GPa on hydrogen-plasma-etched and hydrogen-implanted single-crystalline silicon. International Journal of Hydrogen Energy, 2001, 26, 483-488.	7.1	27
114	Ion beam synthesis of n-type doped SiC layers. Applied Surface Science, 2001, 184, 367-371.	6.1	2
115	Raman scattering structural evaluation of CuInS2 thin films. Thin Solid Films, 2001, 387, 216-218.	1.8	45
116	Microstructural characterisation of CuInS2 polycrystalline films sulfurised by rapid thermal processing. Thin Solid Films, 2001, 387, 219-221.	1.8	8
117	Combined in-depth scanning Auger microscopy and Raman scattering characterisation of CuInS2 polycrystalline films. Vacuum, 2001, 63, 315-321.	3.5	32
118	Effect of Ga incorporation in sequentially prepared CuInS2 thin film absorbers. Solar Energy Materials and Solar Cells, 2001, 67, 97-104.	6.2	39
119	Title is missing!. Journal of Materials Science: Materials in Electronics, 2001, 12, 211-214.	2.2	0
120	Influence of the catalytic introduction procedure on the nano-SnO2 gas sensor performances. Sensors and Actuators B: Chemical, 2001, 79, 98-106.	7.8	162
121	Photoluminescence of Porous Silicon Prepared from Pressure Treated Cz-Si. Physica Status Solidi A, 2000, 182, 401-406.	1.7	0
122	Ultra low energy SIMS, XTEM and X-ray diffraction methods for the characterization of a MBE grown short period (Si Ge)16 superlattices. Thin Solid Films, 2000, 367, 176-179.	1.8	2
123	The aging effect on SnO2â€“Au thin film sensors: electrical and structural characterization. Thin Solid Films, 2000, 371, 249-253.	1.8	89
124	Effect of external stress on creation of buried SiO2 layer in silicon implanted with oxygen. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 73, 134-138.	3.5	13
125	TEM characterisation of high pressureâ€“high-temperature-treated Czochralski silicon samples. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 73, 250-254.	3.5	3
126	Parameter optimisation in SnO2 gas sensors for NO2 detection with low cross-sensitivity to CO: solâ€“gel preparation, film preparation, powder calcination, doping and grinding. Sensors and Actuators B: Chemical, 2000, 65, 166-168.	7.8	44

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127	Influence on the gas sensor performances of the metal chemical states introduced by impregnation of calcinated SnO2 solâ€“gel nanocrystals. Sensors and Actuators B: Chemical, 2000, 68, 94-99.	7.8	77
128	Influence of the completion of oxidation on the long-term response of RGTO SnO2 gas sensors. Sensors and Actuators B: Chemical, 2000, 66, 40-42.	7.8	34
129	MicroRaman scattering from polycrystalline CuInS 2 films: structural analysis. Thin Solid Films, 2000, 361-362, 208-212.	1.8	77
130	Test microstructures for measurement of SiC thin film mechanical properties. Journal of Micromechanics and Microengineering, 1999, 9, 190-193.	2.6	13
131	Analysis of the Thermal Oxidation of Tin Droplets and Its Implications on Gas Sensor Stability. Journal of the Electrochemical Society, 1999, 146, 3527-3535.	2.9	22
132	Î²-SiC on SiO2 formed by ion implantation and bonding for micromechanics applications. Sensors and Actuators A: Physical, 1999, 74, 169-173.	4.1	16
133	Nanoparticle engineering for gas sensor optimisation: improved solâ€“gel fabricated nanocrystalline SnO2 thick film gas sensor for NO2 detection by calcination, catalytic metal introduction and grinding treatments. Sensors and Actuators B: Chemical, 1999, 60, 125-137.	7.8	97
134	Structural and optical characterization of Mn doped ZnS nanocrystals elaborated by ion implantation in SiO2. Nuclear Instruments & Methods in Physics Research B, 1999, 147, 373-377.	1.4	14
135	Luminescence Properties of Oxygen-Containing Silicon Annealed at Enhanced Argon Pressure. Physica Status Solidi (B): Basic Research, 1999, 211, 233-238.	1.5	13
136	Dependence of photoluminescence of silicon on conditions of pressure-annealing. Journal of Alloys and Compounds, 1999, 286, 258-264.	5.5	9
137	Structural analysis of buried conducting CoSi2 layers formed in Si by high-dose Co ion implantation. Journal of Crystal Growth, 1998, 187, 435-443.	1.5	1
138	Correlation between XPS, Raman and TEM measurements and the gas sensitivity of Pt and Pd doped SnO 2 based gas sensors. Fresenius' Journal of Analytical Chemistry, 1998, 361, 110-114.	1.5	116
139	Ion-beam synthesis and structural characterization of ZnS nanocrystals in SiO2. Applied Physics Letters, 1998, 72, 3488-3490.	3.3	24
140	Optical characterization of carbon ion implantation into Si and SiGe alloys. , 1998, 3359, 324.		0
141	Nondestructive assessment of the grain size distribution of SnO2 nanoparticles by low-frequency Raman spectroscopy. Applied Physics Letters, 1997, 71, 1957-1959.	3.3	34
142	Synthesis of SiC Microstructures in Si Technology by High Dose Carbon Implantation: Etchâ€Stop Properties. Journal of the Electrochemical Society, 1997, 144, 2211-2215.	2.9	21
143	Microstructure and morphology of tin dioxide multilayer thin film gas sensors. Sensors and Actuators B: Chemical, 1997, 44, 268-274.	7.8	51
144	Visible photoluminescence of SiO2 implanted with carbon and silicon. Nuclear Instruments & Methods in Physics Research B, 1996, 120, 101-105.	1.4	38

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145	Morphological analysis of nanocrystalline SnO2 for gas sensor applications. Sensors and Actuators B: Chemical, 1996, 31, 1-8.	7.8	195
146	Etchâ€Stop Behavior of Buried Layers Formed by Substoichiometric Nitrogen Ion Implantation into Silicon. Journal of the Electrochemical Society, 1996, 143, 1026-1033.	2.9	4
147	Ionâ€beam synthesis of amorphous SiC films: Structural analysis and recrystallization. Journal of Applied Physics, 1996, 79, 6907-6913.	2.5	51
148	Effect of stress and composition on the Raman spectra of etchâ€stop SiGeB layers. Journal of Applied Physics, 1996, 80, 5736-5741.	2.5	7
149	Point defect reactions in silicon studiedin situby high flux electron irradiation in high voltage transmission electron microscope. Materials Science and Technology, 1995, 11, 1194-1202.	1.6	11
150	Ion beam synthesis of aluminium nitride: characterisation of thin AlN layers formed in microelectronics aluminium. Materials Science and Technology, 1995, 11, 1187-1190.	1.6	2
151	Spectroscopic characterization of phases formed by highâ€dose carbon ion implantation in silicon. Journal of Applied Physics, 1995, 77, 2978-2984.	2.5	33
152	Anisotropic etch-stop properties of nitrogen-implanted silicon. Sensors and Actuators A: Physical, 1994, 45, 219-225.	4.1	4
153	Structural analysis of buried AlN thin films formed by nitrogen implantation into microelectronics grade aluminium. Nuclear Instruments & Methods in Physics Research B, 1994, 84, 214-217.	1.4	7
154	Optical characterisation of SIMOX structures formed by successive implantation and annealing. Nuclear Instruments & Methods in Physics Research B, 1994, 84, 275-280.	1.4	3
155	In-Situ HVEM study of dopant dependent {113}-defect generation in silicon during 1-MeV electron irradiation. Microscopy Research and Technique, 1993, 25, 181-182.	2.2	0
156	On the influence of interfaces and localised stress fields on irradiation-induced point-defect distributions in silicon. Applied Physics A: Solids and Surfaces, 1993, 57, 521-527.	1.4	7
157	In-situ HVEM study of the influence of localised strain, interfaces, and extrinsic point defects on {113}-defect generation in silicon. Physica Status Solidi A, 1993, 138, 417-424.	1.7	4
158	Structural characterisation of nitrogen ion implantation into silicon for sensor technology. Nuclear Instruments & Methods in Physics Research B, 1993, 80-81, 702-705.	1.4	3
159	Analysis of buried etch-stop layers in silicon by nitrogen-ion implantation. Journal of Micromechanics and Microengineering, 1993, 3, 143-145.	2.6	160
160	Microâ€Raman study of stress distribution in local isolation structures and correlation with transmission electron microscopy. Journal of Applied Physics, 1992, 71, 898-906.	2.5	149
161	Dopant Dependent Extended Defect Nucleation and Growth Kinetics in Silicon During 1 Mev Electron Irradiation. Materials Research Society Symposia Proceedings, 1992, 262, 1091.	0.1	2
162	Formation of CoSi2 and TiSi2 on narrow poly-Si lines. Microelectronic Engineering, 1991, 14, 327-339.	2.4	22

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163	On the artificial creation of the EL2 center by means of boron implantation in gallium arsenide. Journal of Applied Physics, 1991, 70, 4202-4210.	2.5	10
164	A tem specimen preparation technique of prespecified areas of semiconductor devices using conventional equipment. Micron and Microscopica Acta, 1990, 21, 223-224.	0.2	0
165	TEM characterisation of lopos structures for submicron CMOS technology. Micron and Microscopica Acta, 1990, 21, 291-292.	0.2	0
166	A fast preparation technique for high-quality plan view and cross-section TEM specimens of semiconducting materials. Ultramicroscopy, 1989, 31, 183-192.	1.9	55
167	Electrical characterisation of nanowires and nanoparticles contacted using a FIB. , 0, , .		0
168	Electrical response of MOSiC gas sensors to CO, NO/sub 2/ and C/sub 3/H/sub 8/. , 0, , .		0
169	Microcoils for biosensors fabricated by focused ion beam (FIB). , 0, , .		2